

Innovative Processing and Synthesis of Ceramics, Glasses, and Composites V

Edited by
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Cover photo: "The SEM images show typical morphology of the spray particles used in this work," is courtesy of R. Gadow, A. Killinger, and C. Li, and appears as figure 4a in the paper "Plasma Sprayed Ceramic Coatings on Glass and Glass Ceramic Substrates," which begins on page 15.

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This volume contains papers presented at a symposium on Innovative Processing and Synthesis of Ceramics, Glasses and Composites held during the 103rd Annual Meeting and Exposition of the American Ceramic Society in Indianapolis, April 22-25, 2001. This symposium provided an international forum for scientists and engineers to discuss all aspects of processing and synthesis of ceramics, glasses and composites. A total of 114 papers, including invited talks, oral presentations, and posters, were presented from 17 countries (the United states, Belgium, Brazil, Canada, Germany, Iran, Israel, Italy, Japan, Mexico, the People's Republic of China, Republic of Korea, Spain, Switzerland, Taiwan, United Kingdom, and Venezuela). The speakers represented universities, industry, and research laboratories.

This volume contains 18 invited and contributed papers, all peer-reviewed according to American Ceramic Society procedures. The latest developments in processing and characterization are covered: CVD/CVI and plasma technology, gas infiltration and polymer processing, rheological behavior, mechanical alloying, reaction forming, functionally graded materials and coatings, laminated object manufacturing, and electronic and magnetic materials. All of the most important aspects necessary for understanding and further development of ceramic processing and characterization are discussed.

The organizers are grateful to all participants and session chairs for their time and effort, to authors for their timely submissions and revisions of the manuscripts, and to reviewers for their valuable comments and suggestions; without the contributions of all involved, this volume would not have been possible. Financial support from the American Ceramic Society is gratefully acknowledged. Thanks are due to the staff of the Meetings and Publications Department of the American Ceramic Society for their tireless efforts. Especially, we greatly appreciate the helpful assistance and cooperation of Sarah Godby throughout the production process of this volume.

We hope that this volume will serve as a useful reference for professionals working in the field of synthesis and processing of ceramics, glasses, and composites.

J. P. Singh Narottam P. Bansal Amit Bandyopadhyay



| rreface |
|---|
| CVD/CVI and Plasma Technology |
| Cubic and Tetragonal Hafnium Oxide Films Prepared by Ion-Beam-Assisted Deposition |
| Plasma-Sprayed Ceramic Coatings on Glass and Glass Ceramic Substrates |
| Gas Infiltration and Preceramic Polymer Processing |
| Manufacturing of Biomorphic SiC Ceramics by Gas Phase Infiltration of Wood |
| Manufacturing of Anisotropic Ceramics from Preceramic Polymer Infiltrated Wood |
| Rheological Behavior |
| Modeling the Dynamic Rheological Behavior of AGAR-Based Aqueous Binders |
| Mechanical Alloying |
| Effects of Alloying with Nb, Re, and Al on Yield Strength of MoSi ₂ |

Reaction Forming In situ Synthesis of Nonoxide-Boron Nitride G. J. Zhang, J. F. Yang, T. Ohji, and S. Kanzaki Fabrication of Lightweight Oxide/Intermetallic Composites at 1000°C by the Displacive P. J. Wurm, P. Kumar, K. D. Ralston, M. J. Mills, and K. H. Sandhage Microstructure and Mechanical Properties of I. Yang, Y. Beppu, G. J. Zhang, and T. Ohji Functionally Graded Materials & Coatings Functionally Graded Porosity in Ceramics—Analysis J. Goebbels, G. Weidemann, R. Dittrich, M. Mangler, and G. Tomandl Novel Processing for Combined Coatings with R. Gadow and D. Scherer Ceramic Coatings on Fiber Woven Fabrics for K.V. Niessen and R. Gadow Laminated Object Manufacturing The Effect of Sheetstock on the Layered Manufacturing A. A. Bender and R. J. Rayne

BaTiO₃-Pt Multilayer Ceramic Capacitors 165

Electronic and Magnetic Materials

S. J. Lombardo, R. V. Shende, and D. S. Krueger

Binder Removal by Supercritical Extraction from

| Processing and Characterization of PZI and PLZI |
|---|
| Thick Films |
| Micromachining of PZT-Based MEMS |
| Templated Grain Growth of Lead Metaniobate Ceramics by Solid Freeform Fabrication |
| Investigation of Ni-Cu-Zn Ferrite with High Performance Derived from Nanoferrite Powders 211 X. Wang, W. Qu, L. Li, Z. Gui, and J. Zhou |
| Index |

CVD/CVI and Plasma Technology

CUBIC AND TETRAGONAL HAFNIUM OXIDE FILMS PREPARED BY ION BEAM ASSISTED DEPOSITION

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ABSTRACT

HfO₂ films were prepared by ion beam assisted deposition (IBAD) of hafnium with simultaneous bombardment with oxygen ions, accelerated between 1-20keV. The ratio between the hafnium arrival rate and the oxygen ion dose, (transport ratio, TR) was varied between 0.5 and 10. Structure and composition were characterized using XRD, XPS, RBS, EPMA.

Two unexpected structures were observed with variation in parameters, a cubic CaF₂-type structure with a parameter of about 0.412nm and a new tetragonal structure, believed to be different from the high temperature HfO₂ structure. The composition of the films was found to be under-stoichiometric, with Hf/O ratio around 1.5. The new tetragonal structure appears to be correlated to low oxygen content, below 1.5. Film orientation could be controlled by varying the substrate rotation during deposition.

INTRODUCTION

Hafnium dioxide has a number of isomorphs and has been the topic of numerous studies. At room temperature the equilibrium phase of hafnia is monoclinic baddeleyte, 1-3 which has the lowest free energy of formation and the largest volume. The effects of stoichiometry and temperature variations under atmospheric and higher pressures have been studied by various authors, and the phase diagram of Hf-O has been determined. 1-3 There is some solubility of O in Hf, but the only oxide phase identified in the phase diagram at room temperature

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was HfO₂, with a phase boundary at about 63.5 at% oxygen.³ At about 1300K, monoclinic HfO₂ transforms into a tetragonal structure and at about 2700K into a cubic structure,^{3,4} of the CaF₂-type⁴. It is interesting to note that Passerini⁵ identified the CaF₂ structure in the HfO₂-CeO₂ system as early as 1930. With increasing pressure, densification of monoclinic HfO₂ occurs by transformation into a number of orthorhombic phases, which have been closely studied and mapped.^{1,2,6,7}.

With the exception of the main phases obtained at atmospheric pressure, other phases were observed in bulk material only under high-pressure conditions. The high-density phases obtained under high-pressure conditions appear to have elastic moduli of the order of 145GPa and are therefore considered among the super-hard materials⁸.

The main interest however in this material is for optical coatings. It presents a relatively high laser damage threshold due to its high melting point, thermal and chemical stability 9,10 and a large transparent range from the IR to the UV (0.22-12 μ m), with a relatively high refractive index, 10 and is also relatively easy to obtain by evaporation. In view of these properties, a number of techniques were used to produce such films, including sol-gel¹¹, atomic layer deposition (ALD)¹², in addition to vacuum deposition methods.

Among the various attempts to obtain high quality optical films, ion beam assisted deposition (IBAD) has also been used in a number of studies, ⁹⁻¹³ with various ion sources, sometimes using ionic species other than oxygen. In connection to the present work, is worth noting that non-stoichiometry of the HfO_x films has been reported¹⁴, but without effects on the structure.

The cubic and tetragonal high temperature structures have been sometimes observed in thin films in small amounts alongside the monoclinic structure. Aarik et al. 12 have reported the presence of the orthorhombic phase in films obtained by the ALD method at 500°C, whereas Ritala et al. 15,16 have observed weak peaks of a tetragonal structure. Recently, Aarik et al. 17 have reported the presence of cubic nano-crystallites on the surface layers of monoclinic HfO₂ films grown by the ALD method at temperatures in the vicinity of 900°C.

The work presented here was undertaken in an attempt to explore the effects of ion bombardment on phase transitions and properties of thin HfO₂ films deposited by IBAD at ion energies of 1-20 keV, significantly higher than ion acceleration energies used in other ^{9,13,14} IBAD works. The bombarding ion was oxygen, but we varied the transport ratio (TR), defined as the ratio between the oxygen flow-rate, and the hafnium evaporation rate. The parameters varied included transport ratio, ion energy, alloying with Ce, substrate cooling and substrate rotation speed. In contradiction with other reports, we obtained films consisting not of a monoclinic

phase with some other high temperature phase, but entirely, or almost entirely of either cubic or tetragonal phase, (which appears to belong to a different space group than the high temperature tetragonal structure of hafnia).

TABLE I - List of samples and experimental conditions

| Sample | Ion Energy | T.R. | Deposition rate | Rotation rate | Composition (O/Hf ratio) | |
|--------|---------------|------|----------------------|------------------|-----------------------------|------------------|
| | keV | | | sec/pass | XPS | EPMA |
| 1 | 20 | 5 | 3.5 | low | 1.30 | 1.44 |
| 2 | 20 | 1 | 0.7 | low | 1.55 | 1.54 |
| 3 | 20 | 10 | 5.3 | low | 1.47 | 1.44 |
| 4 | 20 | 0.5 | 0.3 | low | 1.71 | ••• |
| 6 | 20 | 4 | 2.8 | low | | |
| 7 | 20 | 2 | 1.3 | low | | |
| 8 | 1.0 | 5 | 1.8 | low | 1.74 | |
| 9 | 10 | 5 | 2.9 | low | 1.52 | |
| 11 | 5 | 5 | 2.7 | low | 1.72 | (mages) |
| 20* | 20 | 5 | 3.5 | low | | 1.56 |
| 14 | 20 | 5 | Hf = 3.8, $Ce = 0.3$ | low | | Ce/(Hf+Ce)=0.025 |
| 15 | 1 | 5 | Hf = 1.7, Ce = 0.2 | low | | Ce/(Hf+Ce)=0.021 |
| 16 | 10 | 5 | Hf = 3.9, Ce = 0.5 | low | | |
| 37 | 20 | 5 | 3.4 | 87 | | |
| 36 | 20 | 5 | 3.4 | 50 | | |
| 28 | 20 | 5 | 3.3 | 20 | | 1.27 |
| 35 | 20 | 5 | 3.3 | 0 | | 1.16 |

^{*}This sample was deposited without water-cooling the substrate.

EXPERIMENTAL

A compact IBAD system with a bucket-type 2.45-GHz electron-cyclotron-resonance ion source and an electron beam evaporation source was used for the preparation of the HfO_2 films. The basic details of the ion source have been described elsewhere. ^{18,19} The acceleration voltage of the extracted oxygen ions was varied in the range of 1-20 kV. The ion current density measured with a Faraday cup was typically 26-51 μ A/cm². The base pressure, evacuated with a 1500-l/s cryo-pump was 1-2x 10^{-6} torr. The working pressure of oxygen during the ion source operation was $1-3x10^{-4}$ torr due to gas flow from the ion source. The substrate was maintained at a low temperature by water-cooling the plate under

the substrate holder. The films were obtained on Si (100) wafers by depositing Hf vapor (from a target with purity 98 at%, with the major impurity being Zr) under simultaneous bombardment with oxygen ions. The incidence angle of the oxygen ion beam was normal to the substrate and the hafnium vapor reached the substrate at an angle of approximately 45° from normal. The transport-rate ratio of was varied in the range of 0.5-10. Typical film thickness was in the range of 400-600nm, as measured by surface profilometry. The substrate was rotated during deposition at various speeds varying between 0-3 rpm. (One rotation in 20 sec. is 'high rate' and in 90 sec is considered 'slow').

X-ray diffraction (XRD) data was collected using Cu radiation in a Rigaku Miniflex apparatus at 30 kV-15 mA, with a Ni filter, in the $\theta/2\theta$ mode. The chemical composition was measured using electron probe microanalysis (EPMA). Selected samples were analyzed by X-ray photoelectron spectroscopy (XPS) and Rutherford backscattering (RBS). For standard HfO₂, a powder made by Alfa-Johnson Matthey Gmbh. (Puratronic - 99.988% purity), was used.

Microstructures were obtained (courtesy of Kanagawa High-Technology Foundation (KTF)) using a field emission scanning electron microscope (FE-SEM) capable of ultra high magnification (up to x10⁵).

RESULTS AND DISCUSSION

The experimental conditions for the films discussed here are given in Table I (organized in order of parameter variation). Figure 1a presents the XRD spectrum of sample #1 (20 keV, TR=5). Three strong peaks at about 30, 35 and 50° are observed, with additional small peaks at about 40 and 60° . The three strong peaks together do not belong to any of the ICDD cards for HfO₂ structures. This spectrum, with the exception of the peak at 40° appeared to be typical of a cubic structure, fitting the CaF₂ structure reported by Passerini⁵, and also mentioned in the Pearson handbook.²⁰ A calculated spectrum for such a structure with a_0 =0.506nm is shown in Fig. 1b.

The peaks at 40° and 55° in Fig. 1a are broader than those at 30° and 35° (full width at half maximum -FWHM- is 0.52, compared to 0.32 for the latter two). The broad peaks were de-convoluted using the Gaussian formula and it was determined that this film has a tetragonal rather than cubic structure, with the parameters a=0.5055 and c=0.5111 nm (c/a ratio 1.011). The calculated spectrum of this structure is presented in Fig.1c. As can be observed, this spectrum fits well the spectrum shown in Fig. 1a. The c/a ratio in this structure differs from the value of 1.021 of the normal tetragonal hafnia structure of high-temperature (ICDD card 08-0342). The Miller indices listed in the ICDD card do not correspond to those observed in our film, and this fact, together with the change in the c/a ratio

this leads us to believe that the structure presented here is different from the tetragonal high temperature HfO₂ phase.

On the other hand, by varying ion energy we could obtain films exhibiting the cubic structure. The XRD spectrum of sample no. 8 (1keV, TR5) is shown in Fig. 1d. The additional peak at 40° does not appear here and this spectrum is similar to the cubic XRD profile of Fig. 1b.

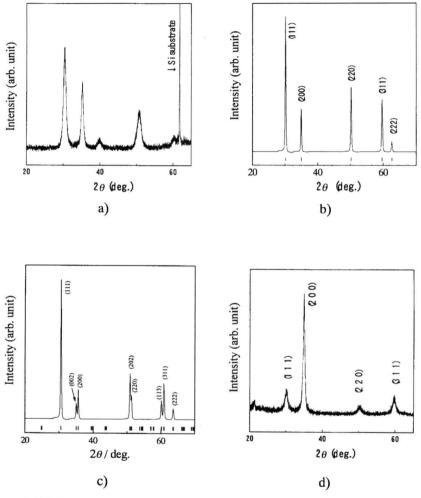


Figure 1. XRD spectra. a) Sample #1; b) Calculated spectrum of the CaF_2 structure with a_0 =0.506nm; c) calculated spectrum of a tetragonal structure fitting Fig. 1a; d) Spectrum of sample #8, fitting the calculated cubic model of Fig. 1b.

A film with a monoclinic structure is shown in Fig. 2, where the XRD spectrum of sample no. 7 is compared to a standard sample for monoclinic HfO₂. The film also presents a certain degree of preferred orientation.

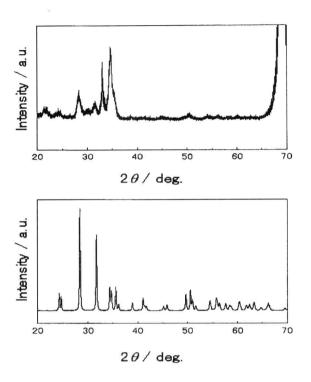


Fig. 2. XRD spectrum of sample #7 (20keV, T.R.2) (top), and comparison with the spectrum of standard monoclinic HfO₂ powder (bottom). The deposited film also contains a second phase –(either cubic or tetragonal, oriented (200)).

Figure 3 presents high-resolution FE-SEM micrographs of three types of films obtained with variation of parameters- samples nos.1, 7 and 14, which are almost entirely tetragonal monoclinic and cubic (oriented), respectively. It should be noted that a small component of a second phase is always present in these samples. All three samples present a columnar structure, but the grains and their spacing are very different. The mechanical properties of these samples are discussed elsewhere²¹. Sample no. 1 (Fig 3 -top) presents a very dense columnar structure and a smooth surface, whereas the monoclinic sample no. 7 (Fig.3-middle) shows